

8. MISCELLANEOUS DIODES

LISTED IN ORDER OF USE, and TYPE No.



LINE No.	TYPE No.	USE	DWG. No.	STATUS	DESCRIPTION
4636t	HCR200P	10	TO5		Si; Complimentary PNP-1A at 80deg.C; VF(off) and VR-200Vmax
4636u	HCR300P	10	TO5		Si; Complimentary PNP-1A at 80deg.C; VF(off) and VR-300Vmax
4636v	HCR400P	10	TO5		Si; Complimentary PNP-1A at 80deg.C; VF(off) and VR-400Vmax
4637	PS592	11			R at 1ma-60ohm; Ib-.10ua at 2V; Ef-.64±10 per cent, Silicon
4638	PS592G	11			R at 1ma-60ohm; Ib-.10ua at 2V; Ef-.64±10 per cent, Silicon
4639	PS594	11			R at 1ma-60ohm; Ib-1ua at 5V; Ef-.62±10 per cent, Silicon
4641	PS595	11			R at 1ma-60ohm; Ib-5ua at 5V; Ef-.62±10 per cent, Silicon
4643	PS645	11			R at 1ma-100ohm; Ib-1ua at 5V; Ef-.62±10 per cent, Silicon
4644	PS645G	11			R at 1ma-100ohm; Ib-1ua at 5V; Ef-.62±5 per cent, Silicon
4644a#	SX10	11			I-Io(e20v-1) over about 5 decades of Current; 100ma at 1.5V max; 300 mW.
4645#	SX640	11	C6		Io(exp 20V-1) over 5 decades of current; 100ma If/1.5Vmax
4646	1N650	12	TO18		Gallium Arsenide; Ip/Iv-15min.; Cap.-40uuf at Ip-10ma.
4647	1N651	12	TO18		Gallium Arsenide; Ip/Iv-10min.; Cap.-40uuf at Ip-10ma.
4648	1N652	12	TO18		Gallium Arsenide; Ip/Iv-5.0min.; Cap.-40uuf at Ip-5.0ma.
4649	1N653	12	TO18		Gallium Arsenide; Ip/Iv-5.0min.; Cap.-60uuf at Ip-5.0ma.
4650	1N2928	12	TO18		Si; Ip-.47ma ± 10 pct; Vp-.065; Ip/Iv-3.5 min.
4651	1N2928A	12	TO18		Si; Ip-.47ma ± 2 pct; Vp-.065; Ip/Iv-3.5 min.
4652	1N2929	12	TO18		Si; Ip-1.0ma ± 10 pct; Vp-.065; Ip/Iv-3.5 min.
4653	1N2929A	12	TO18		Si; Ip-1.0ma ± 2 pct; Vp-.065; Ip/Iv-3.5 min.
4654	1N2930	12	TO18		Si; Ip-4.7ma ± 10 pct; Vp-.065; Ip/Iv-3.5 min.
4655	1N2930A	12	TO18		Si; Ip-4.7ma ± 2 pct; Vp-.065; Ip/Iv-3.5 min.
4656	1N2931	12	TO18		Si; Ip-10ma ± 10 pct; Vp-.065; Ip/Iv-3.5 min.
4657	1N2931A	12	TO18		Si; Ip-10ma ± 2 pct; Vp-.065; Ip/Iv-3.5 min.
4658	1N2932	12	TO18		Si; Ip-22ma ± 10 pct; Vp-.065; Ip/Iv-3.5 min.
4659	1N2932A	12	TO18		Si; Ip-22ma ± 2 pct; Vp-.065; Ip/Iv-3.5 min.
4660	1N2933	12	TO18		Si; Ip-47ma ± 10 pct; Vp-.065; Ip/Iv-3.5 min.
4661	1N2933A	12	TO18		Si; Ip-47ma ± 2 pct; Vp-.065; Ip/Iv-3.5 min.
4662	1N2934	12	TO18		Si; Ip-100ma ± 10 pct; Vp-.065; Ip/Iv-3.5 min.
4663	1N2934A	12	TO18		Si; Ip-100ma ± 2 pct; Vp-.065; Ip/Iv-3.5 min.
4664*	1N2939	12	TO18		Ge; Ip-1.0ma±10pct. at 70mv; Iv-.10ma at 350mv; Ip/Iv-10
4664a∅	1N2939A	12	TO18		Ge; Ip-1.0ma±2.5pct. at 70mv; Iv-.10ma at 350mv; Ip/Iv-10
4665*	1N2940	12	TO18		Ge; Ip-1.0ma±10pct. at 70mv; Iv-.22ma at 350mv; Ip/Iv-8
4665a∅	1N2940A	12	TO18		Ge; Ip-1.0ma±2.5pct. at 70mv; Iv-.22ma at 350mv; Ip/Iv-8
4666*	1N2941	12	TO18		Ge; Ip-4.7ma±10pct. at 70mv; Iv-.60ma at 350mv; Ip/Iv-8
4666a∅	1N2941A	12	TO18		Ge; Ip-4.7ma±2.5pct. at 70mv; Iv-.60ma at 350mv; Ip/Iv-8
4667*	1N2969	12	TO18		Ge; Ip-2.2ma±10pct. at 55mv; Iv-.285ma at 350mv; Ip/Iv-8
4667a∅	1N2969A	12	TO18		Ge; Ip-2.2ma±2.5pct. at 55mv; Iv-.285ma at 350mv; Ip/Iv-8
4668	1N3114	12	TO18		GaAs; Ip-2.2ma; Ip/Iv-10 min.
4669	1N3114A	12	TO18		GaAs; Ip-2.2ma ± 2 pct; Ip/Iv-10 min.
4670	1N3115	12	TO18		GaAs; Ip-2.2ma; Ip/Iv-10 min.
4671	1N3115A	12	TO18		GaAs; Ip-2.2ma ± 2 pct; Ip/Iv-10 min.
4672	1N3116	12	TO18		GaAs; Ip-4.7ma; Ip/Iv-10 min.
4673	1N3116A	12	TO18		GaAs; Ip-4.7ma ± 2 pct; Ip/Iv-10 min.
4674	1N3117	12	TO18		GaAs; Ip-4.7ma; Ip/Iv-10 min.
4675	1N3117A	12	TO18		GaAs; Ip-4.7ma ± 2 pct; Ip/Iv-10 min.
4676	1N3118	12	TO18		GaAs; Ip-10ma; Vp-160mv; Vv-600mv; Ip/Iv-15
4677	1N3118A	12	TO18		GaAs; Ip-10ma ± 2 pct; Vp-160mv; Vv-600mv; Ip/Iv-15
4678	1N3119	12	TO18		GaAs; Ip-10ma; Vp-160mv; Vv-600mv; Ip/Iv-15
4679	1N3119A	12	TO18		GaAs; Ip-10ma ± 2 pct; Vp-160mv; Vv-600mv; Ip/Iv-15
4680	1N3120	12	TO18		GaAs; Ip-2.2ma; Vp-160mv; Vv-600mv; Ip/Iv-15
4681	1N3120A	12	TO18		GaAs; Ip-2.2ma ± 2 pct; Vp-160mv; Vv-600mv; Ip/Iv-15
4682	1N3128	12			Germanium; Ip - 5.0ma; Ip/Iv - 8 min.
4683	1N3129	12			Germanium; Ip - 20ma; Ip/Iv - 8 min.
4684	1N3130	12			Germanium; Ip - 50ma; Ip/Iv - 8 min.
4685	1N3138	12			Gallium-Arsenide; Ip - 50ma; Ip/Iv - 20 min.
4685a∅	1N3149	12	TO18		Ge; Ip-10ma±10pct. at 70mv; Iv-1.3ma at 350mv; Ip/Iv-8
4685b∅	1N3149A	12	TO18		Ge; Ip-10ma±2.5pct. at 70mv; Iv-1.3ma at 350mv; Ip/Iv-8
4685c∅	1N3150	12	TO18		Ge; Ip-22ma±10pct. at 70mv; Iv-2.85ma at 350mv; Ip/Iv-8
4685d∅	1N3218	12			Ge; Ip-1.0ma±10pct. at 60mv; Iv-.13ma at 350mv; Cap-7pf.
4685e∅	1N3218A	12			Ge; Ip-1.0ma±10pct. at 60mv; Iv-.13ma at 350mv; Cap-4pf.
4685f∅	1N3219	12			Ge; Ip-2.2ma±10pct. at 60mv; Iv-.28ma at 350mv; Cap-14pf.
4685g∅	1N3219A	12			Ge; Ip-2.2ma±10pct. at 60mv; Iv-.28ma at 350mv; Cap-7pf.

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4686	1T1023	12			Ge; Ip-2ma±10pct; Iv-.44ma max; Ip/Iv-5.0 min.
4686aØ#	1T1101	12	M27		Ge; Ip-2.0ma; Vp-70mv; Ip/Iv-8; Pc-25mw.
4686bØ#	1T1102	12	M27		Ge; Ip-2.0ma; Vp-70mv; Ip/Iv-5.5; Pc-25mw.
4686cØ#	1T1103	12	M27		Ge; Ip-2.0ma; Vp-70mv; Ip/Iv-7; Pc-25mw.
4687	D4115	12	F10		Ipk-1.8ma; Rser-1 ohm/150ma; Cap-8uuf/350mv; Fosc-2.KMc min. Ge; Ip/Iv-5min; Vpk-55mv; Vvalley-350mv; Lser-.40muH.
4688	D4115A	12	F10		Ipk-1.7ma; Rser-2 ohm/150ma; Cap-6uuf/350mv; Fosc-3.KMc min. Ge; Ip/Iv-5min; Vpk-55mv; Vvalley-350mv; Lser-.40muH.
4689	D4115B	12	F10		Ipk-1.6ma; Rser-3 ohm/150ma; Cap-4uuf/350mv; Fosc-4.KMc min. Ge; Ip/Iv-5min; Vpk-55mv; Vvalley-350mv; Lser-.40muH.
4689aØ	D4168C	12			Ge; Ip-3.5ma; Vp-150mv; Ip/Iv-5min.; fosc-8KMc.
4689bØ	D4168D	12			Ge; Ip-3.5ma; Vp-150mv; Ip/Iv-5min.; fosc-10KMc.
4689cØ	HF1000	12	TO18		Ip-1-2ma at 49mv; Ip/Iv-5.0min; Cd-15pf; Freq. 500Mc.
4689dØ	HF1001	12	TO18		Ip-1-2ma at 49mv; Ip/Iv-7.0min; Cd-15pf; Freq. 500Mc.
4689eØ	HF1002	12	TO18		Ip-1.0±.05ma at 49mv; Ip/Iv-8.5min; Cd-10pf; Freq. 500Mc.
4689fØ	HF1003	12	TO18		Ip-5.0±.25ma at 49mv; Ip/Iv-8.5min; Cd-50pf; Freq. 500Mc.
4689gØ	HF1004	12	TO18		Ip-10±.50ma at 49mv; Ip/Iv-8.5min; Cd-100pf; Freq. 500Mc.
4690	HT1	12	TO18		Si.; Ip/Iv-3.5 min; Ip-1ma at 65V.
4691	HT2	12	TO18		Si.; Ip/Iv-3.5 min; Ip-1.2ma at 65V.
4692	HT3	12	TO18		Si.; Ip/Iv-3.5 min; Ip-1.5ma at 65V.
4693	HT4	12	TO18		Si.; Ip/Iv-3.5 min; Ip-1.8ma at 65V.
4694	HT5	12	TO18		Si.; Ip/Iv-3.5 min; Ip-2.2ma at 65V.
4695	HT6	12	TO18		Si.; Ip/Iv-3.5 min; Ip-2.7ma at 65V.
4696	HT7	12	TO18		Si.; Ip/Iv-3.5 min; Ip-3.3ma at 65V.
4697	HT8	12	TO18		Si.; Ip/Iv-3.5 min; Ip-3.9ma at 65V.
4698	HT9	12	TO18		Si.; Ip/Iv-3.5 min; Ip-4.7ma at 65V.
4699	HT10	12	TO18		Si.; Ip/Iv-3.5 min; Ip-5.6ma at 65V.
4700Ø#	JK9A	12			Ge; Ip-.90ma min; Ip/Iv-2min; Vp-45mv; Vv-170mv.
4700aØ#	JK10A	12			Ge; Ip-4.5ma min; Ip/Iv-2min; Vp-50mv; Vv-50mv.
4700bØ#	JK11A	12			Ge; Ip-13.5ma min; Ip/Iv-2min; Vp-55mv; Vv-270mv.
4701Ø#	JK19A	12			Ge; Ip-.90ma min; Ip/Iv-5min; Vp-55mv; Vv-290mv.
4701aØ#	JK20A	12			Ge; Ip-4.5ma min; Ip/Iv-5min; Vp-55mv; Vv-300mv.
4702Ø#	JK21A	12			Ge; Ip-13.5ma min; Ip/Iv-5min; Vp-55mv; Vv-310mv.
4703	T101	12			Peak I-.80ma; Peak V-55mv; Valley-300mv; IP/IV-4.5 min.
4704	T102	12			Peak I-1.5ma; Peak V-55mv; Valley-300mv; IP/IV-4.5 min.
4705	T103	12			Peak I-3.5ma; Peak V-55mv; Valley-300mv; IP/IV-4.5 min.
4706	T104	12			Peak I-7.0ma; Peak V-55mv; Valley-300mv; IP/IV-4.5 min.
4707	T105	12			Peak I - 15ma; Ip/Iv - 5 min.
4708*	T1925	12	C16		Ge; Ip-1.0ma±2.5pct; C-9pf; Ip/Iv-5min; Self res. f-1.9KMc.
4708aØ	T1975	12	C16		Ge; Ip-1.0ma±2.5pct; C-11pf; Ip/Iv-8min; Self res. f-1.9KMc.
4708bØ	T1976	12	C16		Ge; Ip-5.0ma±2.5pct; C-45pf; Ip/Iv-6min; Self res. f-800KMc.
4709	TD1	12	TO9		Ge.; Ip/IV - 3 min; Ip-2ma at 50 mV.
4710	TD2	12			Germanium; Ip/Iv-5 min; Ip-2ma at 50mv.
4711	TD3	12			Germanium; Ip/Iv-7 min; Ip-2ma at 50mv.
4712	TD4	12			Ge; Ip/Iv-5 min; Ip-18ma to 22ma at 50mv, Tr-6nsec max.
4712aØ	TD5	12			Ip/Iv-8; Ip-20ma; Switch speed .8n sec.
4712bØ	TD5A	12			Ip/Iv-12; Ip-20ma; Switch speed .8n sec.
4712cØ	TD6	12			Ip/Iv-8; Ip-10ma; Switch speed .8n sec.
4712dØ	TD6A	12			Ip/Iv-12; Ip-10ma; Switch speed .8n sec.
4712eØ	TD7	12			Ip/Iv-8; Ip-5.0ma; Switch speed .8n sec.
4712fØ	TD7A	12			Ip/Iv-12; Ip-5.0ma; Switch speed .8n sec.
4712gØ	TD8	12			Ip/Iv-8; Ip-1.0ma; Switch speed 3.0n sec.
4712hØ	TD8A	12			Ip/Iv-12; Ip-1.0ma; Switch speed 3.0n sec.
4712iØ	TD12	12	TO18		Ge; Ip-1.02ma max.; Vp-55mv; Vv-325mv; Ip/Iv-8.0
4712jØ	TD15	12	TO18		Ge; Ip-1.05ma max.; Vp-55mv; Vv-325mv; Ip/Iv-8.0
4712kØ	TD22	12	TO18		Ge; Ip-2.0ma; Ip/Iv-9.0; Vf-465mv.
4712mØ	TD25	12	TO18		Ge; Ip-2.0ma; Ip/Iv-9.0; Vf-465mv.
4712nØ	TD52	12	TO18		Ge; Ip-5.1ma max.; Vp-55mv; Vv-325mv; Ip/Iv-8.0
4712pØ	TD55	12	TO18		Ge; Ip-5.25ma max.; Vp-55mv; Vv-325mv; Ip/Iv-8.0
4713	TD100	12			Developmental: V. Range neg. slope-65-280mV; Peak I-1.5-7.6ma
4714	TD101	12			Developmental: V. Range neg. slope-65-280mV; Peak I-1.5-3.1ma
4715	TD102	12			Developmental: V. Range neg. slope-65-280mV; Peak I-2.9-5.2ma
4715aØ	TD102	12	TO18		Ge; Ip-10ma; Ip/Iv-9.0; Vf-485mv.

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4716	TD103	12			Developmental:V.Range neg.slope-65-280mV;Peak I-4.2-7.6ma
4717	TD104	12			Developmental:V.Range neg.slope-65-280mV;Peak I-1.5-2.1ma
4718	TD105	12			Developmental:V.Range neg.slope-65-280mV;Peak I-1.9-2.5ma
4718aØ	TD105	12	TO18		Ge; Ip-10ma; Ip/Iv-9.0; Vf-485mv.
4719	TD106	12			Developmental:V.Range neg.slope-65-280mV;Peak I-2.3-3.1ma
4720	TD107	12			Developmental:V.Range neg.slope-65-280mV;Peak I-2.9-3.7ma
4721	TD108	12			Developmental:V.Range neg.slope-65-280mV;Peak I-3.5-4.4ma
4722	TD109	12			Developmental:V.Range neg.slope-65-280mV;Peak I-4.2-5.2ma
4723	TD110	12			Developmental:V.Range neg.slope-65-280mV;Peak I-5.0-6.3ma
4723aØ	TD110	12	TO18		Ge; Ip-1.1ma max.;Vp-55mv;Vv-325mv;Ip/Iv-10
4724	TD111	12			Developmental:V.Range neg.slope-65-280mV;Peak I-6.1-7.6ma
4724aØ	TD202	12	TO18		Ge; Ip-20ma; Ip/Iv-9.0; Vf-510mv.
4724bØ	TD205	12	TO18		Ge; Ip-20ma; Ip/Iv-9.0; Vf-510mv.
4724cØ	TD210	12	TO18		Ge; Ip-2.0ma; Ip/Iv-11; Vf-465mv.
4724dØ	TD502	12	TO18		Ge; Ip-50ma; Ip/Iv-9.0; Vf-550mv.
4724eØ	TD505	12	TO18		Ge; Ip-50ma; Ip/Iv-9.0; Vf-550mv.
4724fØ	TD510	12	TO18		Ge; Ip-5.5ma max.;Vp-55mv;Vv-325mv;Ip/Iv-10
4724gØ	TD1010	12	TO18		Ge; Ip-10ma; Ip/Iv-11; Vf-485mv.
4724hØ	TD2010	12	TO18		Ge; Ip-20ma; Ip/Iv-11; Vf-510mv.
4724jØ	TD5010	12	TO18		Ge; Ip-50ma; Ip/Iv-11; Vf-550mv.
4724kØ#	THP917	12			GaAs; Ip-5ma at 140mv; Iv-.5ma at 600mv.
4724mØ#	THP921	12			Ge; Ip-1ma at 55mv; Iv-.125ma at 325mv.
4725	WX822A	12			Ip-2.0±5 pct; Iv-.32ma; Ip/Iv-8.0
4726	WX822B	12			Ip-5.0±3 pct; Iv-.8ma; Ip/Iv-8.0
4726aØ	XA650	12			GaAs; Ip-10ma±10pct.;Ip/Iv-15.
4726bØ	XA651	12			GaAs; Ip-10ma±3pct.;Ip/Iv-10.
4726cØ	XA652	12			GaAs; Ip-5ma±10pct.;Ip/Iv-5.
4726dØ	XA653	12			GaAs; Ip-5ma±10pct.;Ip/Iv-5.
4726eØ#	YS10	12	TO18		Ge.; Ip/Iv-5.0min; Ip-7.0ma at 50mV.; Valley-300mv.
4727	HU5	13	TO18		Si;IF-.50ma min at .25V; IR-5.0ua max at 0-.50V.
4728	HU5A	13	TO18		Si;IF-.50ma min at .25V; IR-5.0ua max at 0-.50V;Cmax-10pf
4729	HU10	13	TO18		Si;IF-1.0ma min at .25V; IR-10ua max at 0-.50V.
4730	HU10A	13	TO18		Si;IF-1.0ma min at .25V; IR-10ua max at 0-.50V;Cmax-20pf
4731	HU25	13	TO18		Si;IF-2.5ma min at .25V; IR-25ua max at 0-.50V.
4732	HU25A	13	TO18		Si;IF-2.5ma min at .25V; IR-25ua max at 0-.50V;Cmax-50pf
4733	HU50	13	TO18		Si;IF-5.0ma min at .25V; IR-50ua max at 0-.50V.
4734	HU50A	13	TO18		Si;IF-5.0ma min at .25V; IR-50ua max at 0-.50V;Cmax-100pf
4735	HU75	13	TO18		Si;IF-7.5ma min at .25V; IR-75ua max at 0-.50V.
4736	HU75A	13	TO18		Si;IF-7.5ma min at .25V; IR-75ua max at 0-.50V;Cmax-150pf
4737	HU100	13	TO18		Si;IF-10ma min at .25V; IR-100ua max at 0-.50V.
4738	HU100A	13	TO18		Si;IF-10ma min at .25V; IR-100ua max at 0-.50V;Cmax-200pf
4738aØ#	JK100A	13			Ge; If-5.0ma min.; Ir-10ua typ; 200mv.
4738bØ	CK1101	14	M23		4 term. photo-sens. switch. device;Switch on time-.80msec.
4738cØ	CK1102	14	M23		4 term. photo-sens. switch. device;Switch on time-40msec.
4738dØ	CK1103	14	M23		4 term. photo-sens. switch. device;Switch on time-22msec.
4738eØ	CK1104	14	M23		4 term. photo-sens. switch. device;Switch on time-55msec.
4738fØ	2N1966	15			Ge; Turn-on I-.5ma; Sustaining I-20ma max.
4738gØ	2N1967	15			Ge; Turn-on I-.5ma; Sustaining I-20-80ma.
4738hØ	2N1968	15			Ge; Turn-on I-.3ma; Sustaining I-5ma max.
4739	1N79	M			Meter Rectifier up to 3000 Mc.
4740	1N830	M	A1		Micro-min diode Rect. Efficiency at 100Mc-65 percent min.
4741	1N2326	M			For temperature and voltage compensation applications, For use with 2N217, 2N270, 2N408 or similar types.
4741aØ	1N3192	M			Blow-Out Diode; 5.8A (Pulse).
4742#	1S35	M			Matched Quad Germanium.
4743#	1S57	M			Si; Protected I-10ma min at .80V.; IR-.50ua max.
4744#	1S58	M			Matched Quad Germanium.
4745	1T51	M			Thermal Compensation Diode;Thermal Coeff.-.002V/deg.C at 1.2ma;PIV-25V;Fwd. Eb-0.11V at 1.2ma; Avg. If-100ma
4746	1T52	M			Thermal Compensation Diode;Thermal Coeff.-.202V/deg.C at 1.2ma;PIV-25V;Fwd. Eb-0.13V at 1.2ma;Avg. If-25ma
4747	6GC1	M			Se. Double Diode for discriminator or phase detector; If-1.1ma min. at 2.5V; Ir-4ua at 20V.